

| L Number | Hits | Search Text | DB | Time stamp |
|----------|------|--|---|------------------|
| 1 | 21 | (Forming near (NMOS or PMOS)).ti. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/10/31 12:53 |
| 2 | 4364 | ((438/724) or (438/287) or (438/762) or (438/763) or (438/775) or (438/776) or (438/777)).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/10/31 12:54 |
| 3 | 326 | ((438/724) or (438/287) or (438/762) or (438/763) or (438/775) or (438/776) or (438/777)).CCLS.) and CMOS | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/10/31 12:54 |
| 4 | 1165 | ((438/724) or (438/287) or (438/762) or (438/763) or (438/775) or (438/776) or (438/777)).CCLS.) and transistor | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/10/31 12:54 |
| 5 | 171 | ((438/724) or (438/287) or (438/762) or (438/763) or (438/775) or (438/776) or (438/777)).CCLS.) and transistor) and (substrate with conductivity) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/10/31 14:05 |
| 6 | 1219 | MOS and transistor and (substrate with conductivity) and (etch\$3 with (gate near oxide)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/10/31 14:06 |
| - | 43 | Kraft.in. and nitride | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/10/31 12:49 |